

3DD259(260,261), 3DD262(263)**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications				
			3DD259			3DD262	
			A	B	C	D	E
Collector-Emitter Voltage	V_{CEO}	V	300	400	500	600	700
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	300	400	500	600	700
Emitter-Base Voltage	V_{EBO}	V	5			5	
Max. Collector Current	I_{CM}	A	3.5			5	
Max. Collector Dissipation	P_{CM}	W	50 ($T_c \leq 75^\circ C$)			75 ($T_c \leq 75^\circ C$)	
Junction Temperature	T_{jm}	$^\circ C$	175				
Storage Temperature	T_{stg}	$^\circ C$	-55~+175				
Collector-Emitter Leakage Current	I_{CEO}	mA	1.0 ($V_{CE}=100V$)				
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.5 ($I_C=1.75A, I_B=0.35A$)			1.5 ($I_C=2.5A, I_B=0.5A$)	
DC Current Gain	h_{FE}		Max.:180,Min.:7 ($V_{CE}=10V, I_C=1.75A$)			Max.:180, Min.:7 ($V_{CE}=10V, I_C=2.5A$)	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 5 ($I_E=0.5mA$)			≥ 5 ($I_E=2mA$)	

hFE Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	7~15	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions: